What is the right form of the probability distribution of the conductance at the mobility edge?

In a recent letter, Slevin and Ohtsuki [1] reported finite size scaling results for the Anderson metal to insulator transition for the orthogonal and unitarity classes of the single electron tight-binding(TB) model. The average value of the conductance $G=(e^2/h)g$ at the mobility edge, as well as the distribution of the conductance at the critical point, $p_c(g)$, were calculated. Their studies showed that $p_c(g)$ is independent of the system size. It also does not show any dip around g=0, as the ϵ expansion results [2] suggest. These conclusions were based on numerical results of system sizes of N x N x N, with N=6,8 and 10. We will present new numerical data that indeed shows that $p_c(g)$ has a dip for small g.

We have systematically studied the conductance G of the 3d TB model by using the transfer matrix technique [3], which relates the conductance G with the transmission matrix t, i.e. $G=(e^2/h)g$, with $g=2Tr(tt^{\dagger})$. The g defined here is for both spins. In Fig. 1 we present the results of $p_c(g)$ for three different sizes of N=5, 10, and 20.

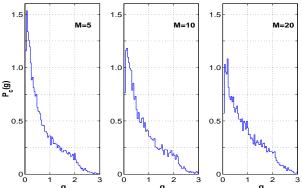


FIG. 1. The distribution of g at the critical point for three different sizes

The mobility edge [1] is at W=16.5 and E=0.0. Notice that as the size of the system increases a dip is developed at g=0, which is not present in the results presented in Fig. 2 of Ref. 1. We therefore have a size dependent $p_c(g)$. which has a dip at small g. It is well known that p(g) for extended states is gaussian, while for localized states is log-normal. However, it is not well known either experimentally [4] or theoretically what is the correct form of the probability distribution at the mobility edge. $p_c(g)$ obtained [2] in the ϵ expansion in the field theory has a hole at small g in agreement with the numerical results presented here. Recent results [5] for a 2d TB model in the presence of a strong magnetic field show that $p_c(g)$ is very broad with a dip at small g. The 2d $p_c(g)$ is very different from the 3d $p_c(g)$ presented here. We have also calculated the average value of the conductance at the critical point (E=0.0 and W=16.5) for N=5, 10 and 20 for 20000, 10000 and 8000 random configurations respectively. The results are summarized in table I.

TABLE I. The means and standard deviations of the critical distribution of g and ln g.

	_	_		
N	< g >	σ_q	< lng >	σ_{lng}
5	0.72	0.64	-0.857	1.19
10	0.78	0.66	-0.727	1.11
20	0.86	0.68	-0.587	1.09

Notice that both g and lng have very large standard deviations, as big as their average values. Our results for both $\langle g \rangle$ and $\langle g \rangle_g = e^{\langle lng \rangle}$ for the N=10 case (0.78, 0.48) are larger than the results presented (0.58, 0.30) in table III of Ref. 1 for the same model. This difference might be due [6] to the different boundary conditions used by Ref. 1 (fixed) and ourselves (periodic). For the 2d case [5] it is shown that $\langle g \rangle$ =1.00 and $\langle g \rangle_g$ =0.88 for the infinite size system. If we extrapolate our finite-size results to infinite sizes we obtain that $\langle g \rangle$ =1.00 and $\langle g \rangle_g$ =0.70. Remember that σ_g is comparable to $\langle g \rangle$.

In summary, we have numerically calculated the full probability distribution of the conductance, $p_c(\mathbf{g})$, at the Anderson critical point. We find that $p_c(\mathbf{g})$ has a dip at small g in agreement with the ϵ expansion results [2]. The $p_c(\mathbf{g})$ for the 3d system is quite different from that of the 2d quantum critical point [5]. The universality or not of these distributions is of central importance to the field of disordered systems.

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